

## FNK N-Channel Enhancement Mode Power MOSFET

### Description

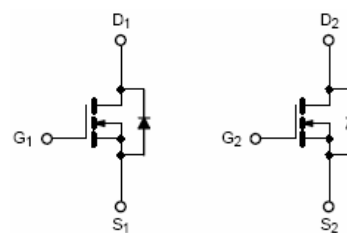
The FNK9928 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

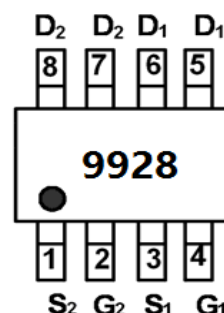
- $V_{DS} = 20V, I_D = 9A$   
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = 4.5V$   
 $R_{DS(ON)} < 18m\Omega @ V_{GS} = 2.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current

### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



SOP-8 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
9928	FNK9928	SOP-8	Ø330mm	12mm	2500 units

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Drain Current-Continuous	$I_D$	9	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D (100^\circ C)$	3.8	A
Pulsed Drain Current	$I_{DM}$	36	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	100	$^\circ C/W$
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**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

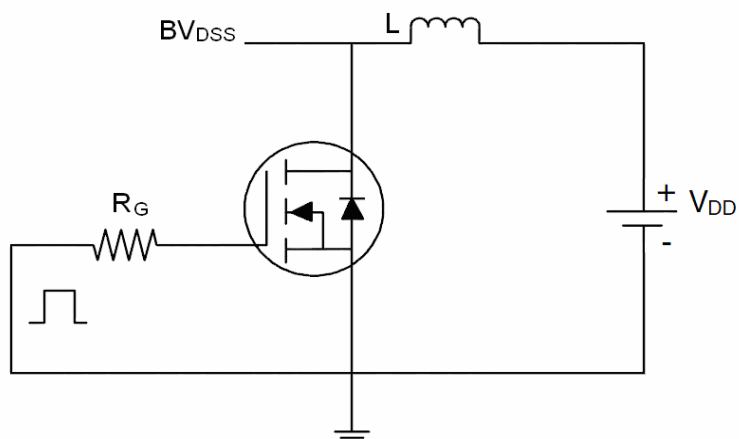
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	22	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	9.7	14	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A	-	12	18	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	20	-	-	S
Dynamic Characteristics <sup>(Note4)</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, F=1.0MHz	-	640	-	PF
Output Capacitance	C <sub>OSS</sub>		-	140	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	80	-	PF
Switching Characteristics <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =1A V <sub>GEN</sub> =4.5V, R <sub>G</sub> =6Ω	-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	9	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3A, V <sub>GS</sub> =4.5V	-	10	-	nC
Gate-Source Charge	Q <sub>GS</sub>		-	1.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1.7A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	6	A

**Notes:**

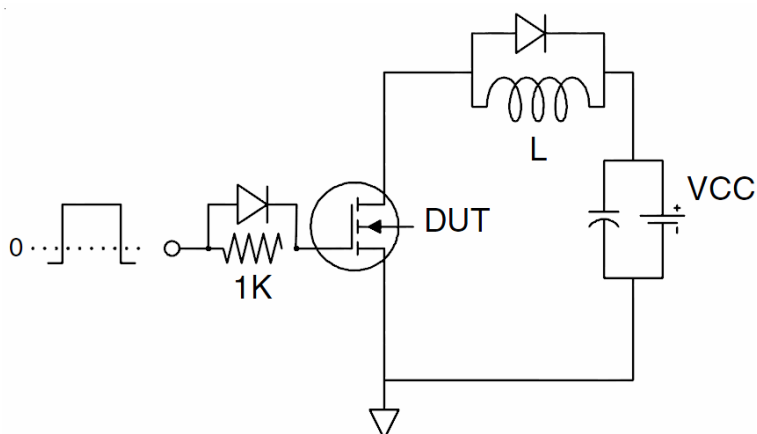
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

## Test Circuit

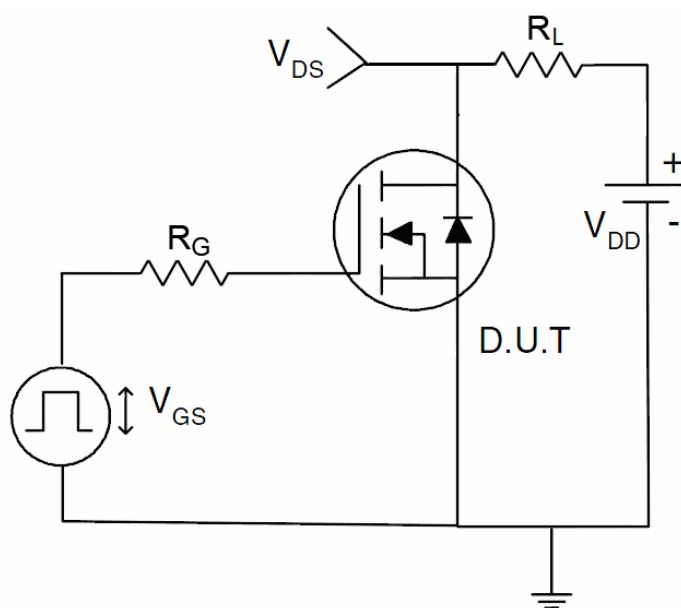
### 1) $E_{AS}$ Test Circuits



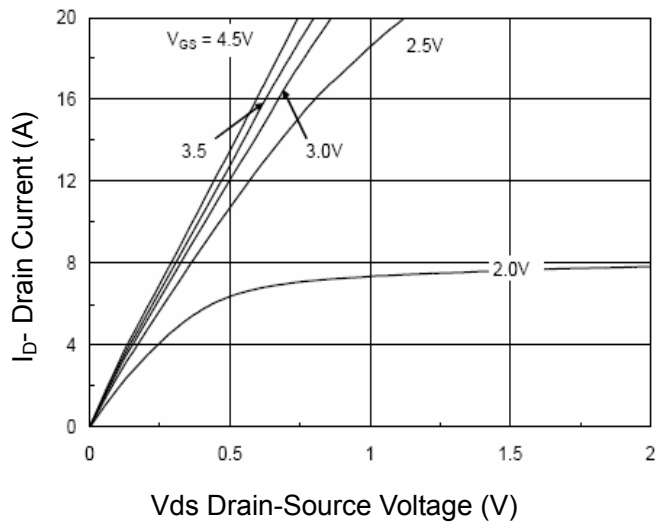
### 2) Gate Charge Test Circuit:



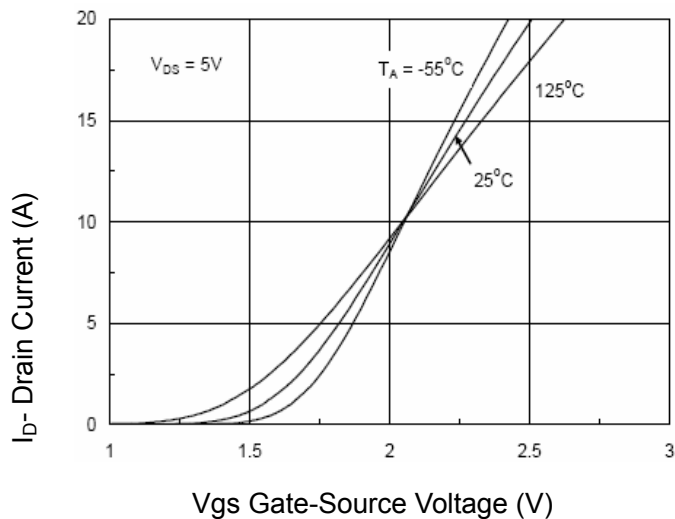
### 3) Switch Time Test Circuit:



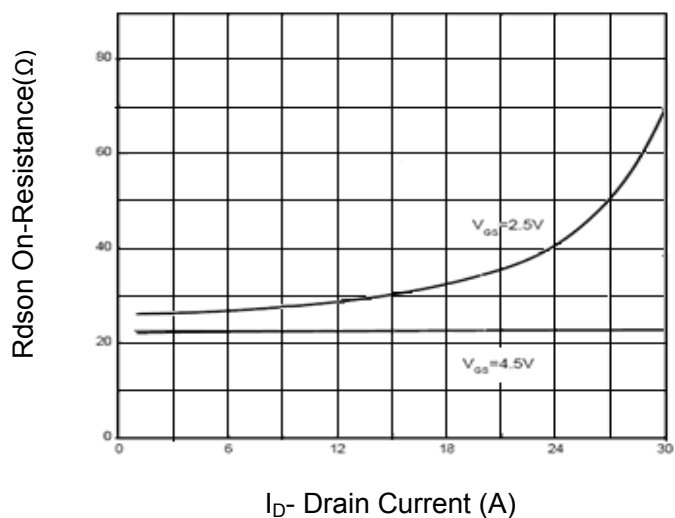
### Typical Electrical and Thermal Characteristics (Curves)



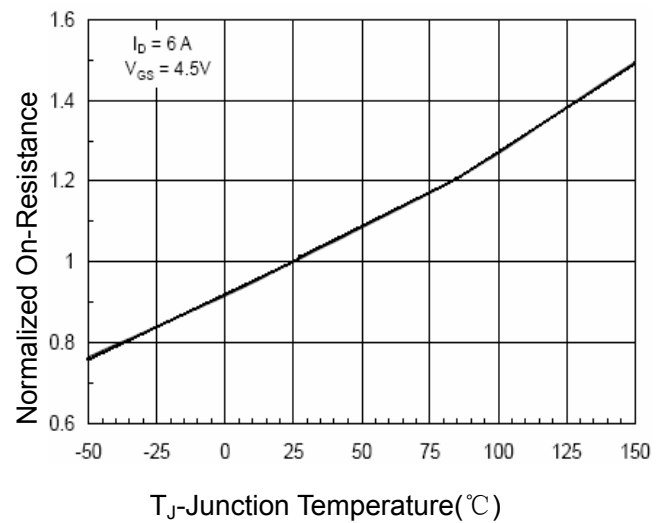
**Figure 1 Output Characteristics**



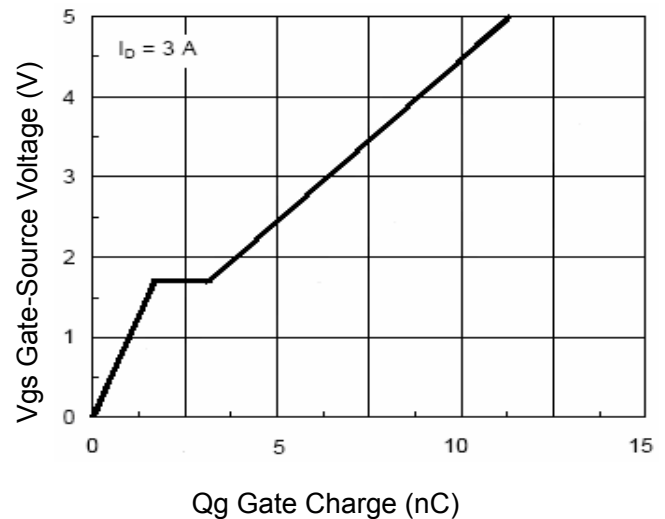
**Figure 2 Transfer Characteristics**



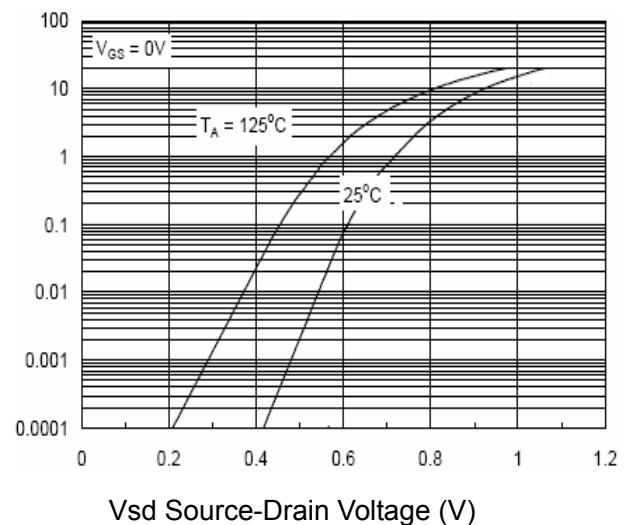
**Figure 3 Rdson- Drain Current**



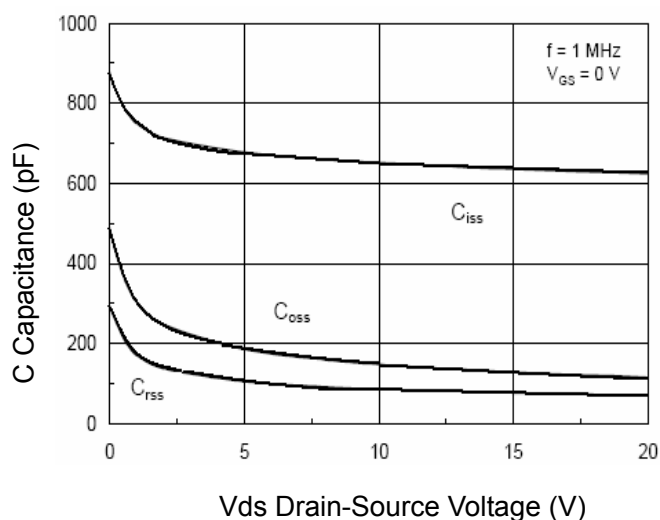
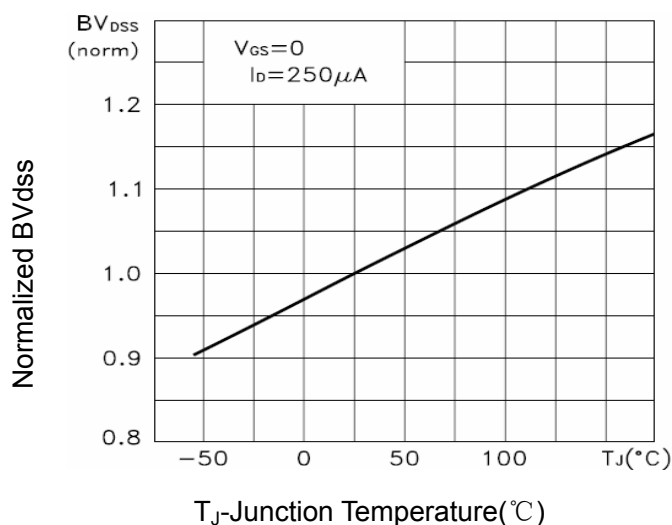
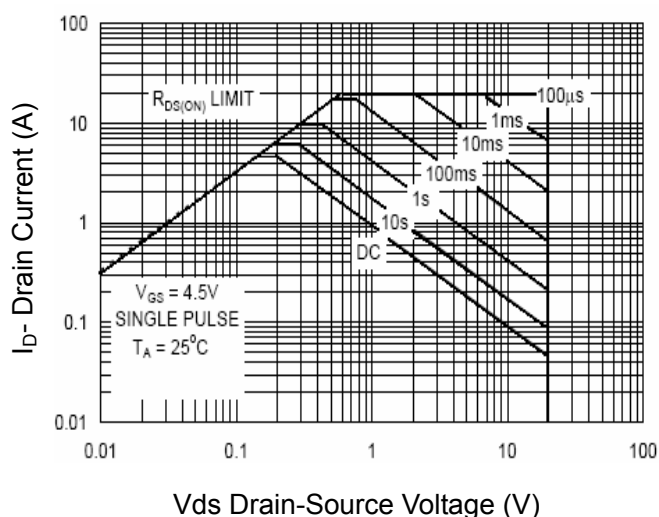
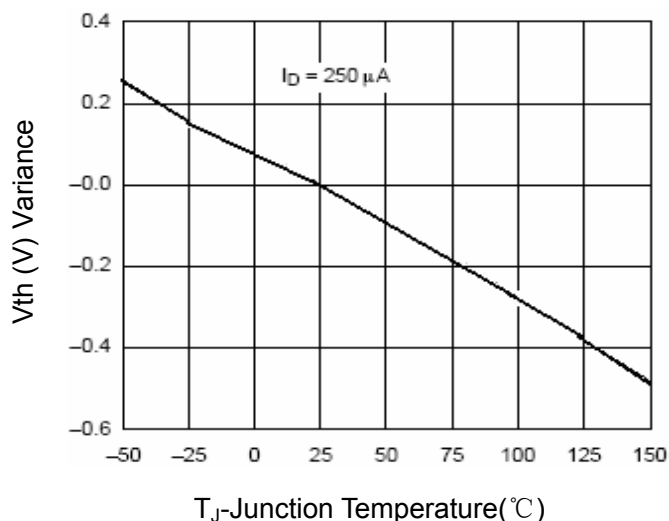
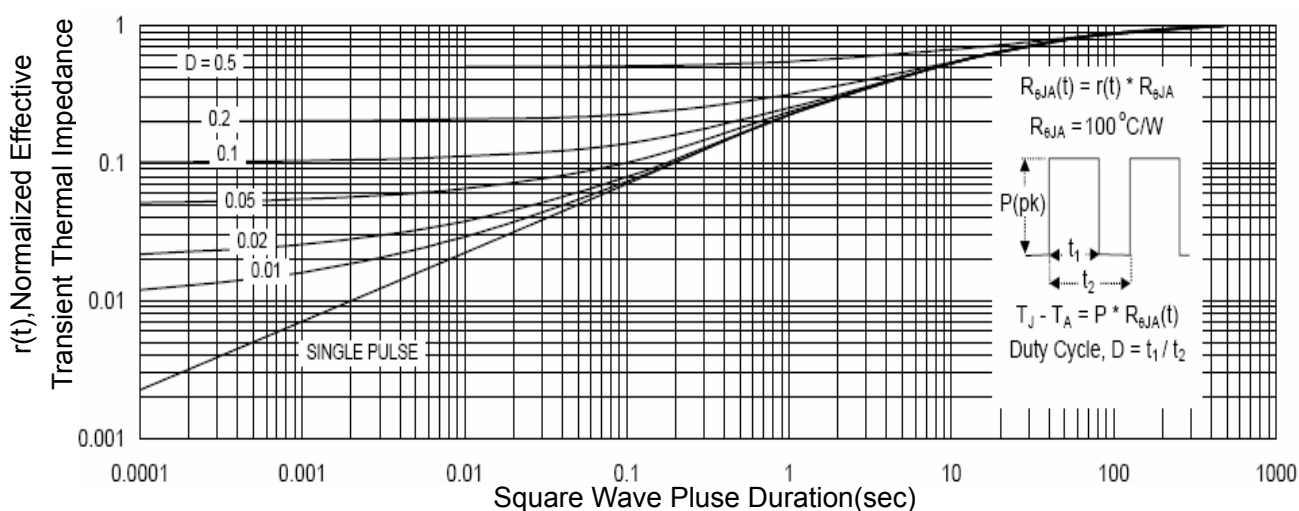
**Figure 4 Rdson-Junction Temperature**

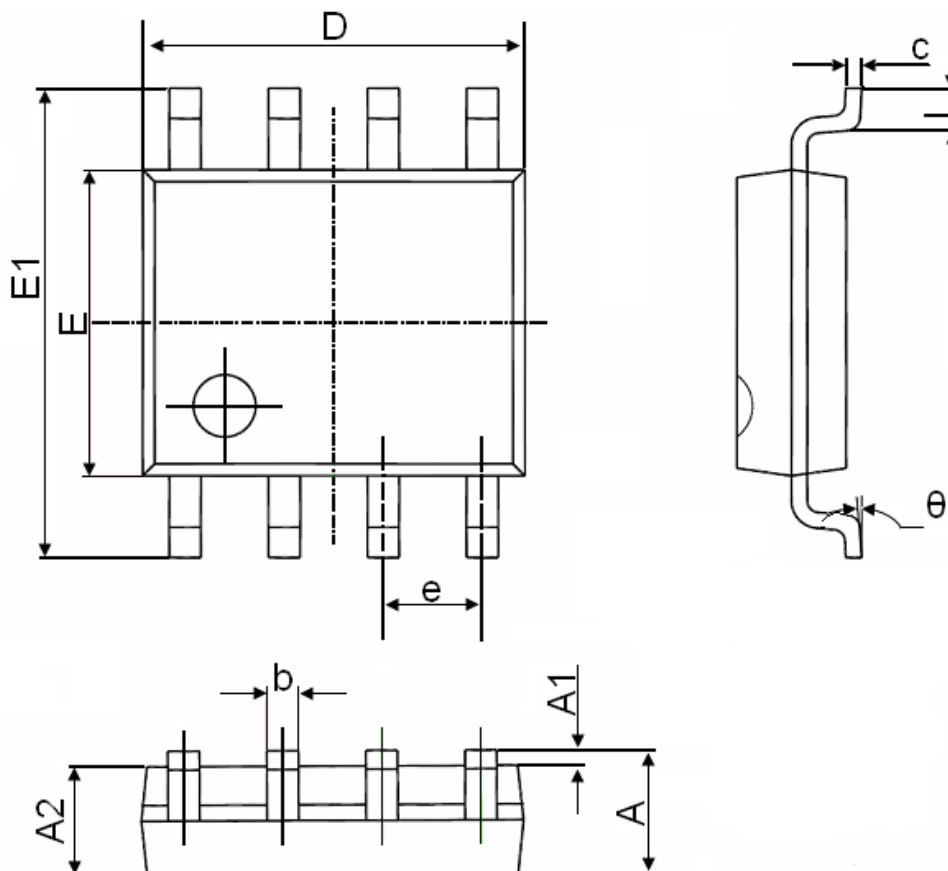


**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**


**Figure 7 Capacitance vs Vds**

**Figure 9  $BV_{DSS}$  vs Junction Temperature**

**Figure 8 Safe Operation Area**

**Figure 10  $V_{GS(th)}$  vs Junction Temperature**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

**SOP-8 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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